

# Low $V_{CE(sat)}$ IGBT High Speed IGBT

IXSH/IXSM 30N60  
IXSH/IXSM 30N60A

$V_{CES}$	$I_{C25}$	$V_{CE(sat)}$
600 V	50 A	2.5 V
600 V	50 A	3.0 V

## Short Circuit SOA Capability

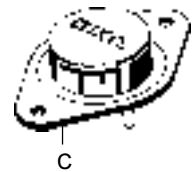


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1\text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	50	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	30	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	100	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15\text{ V}$ , $T_J = 125^\circ\text{C}$ , $R_G = 4.7\ \Omega$ Clamped inductive load, $L = 100\ \mu\text{H}$	$I_{CM} = 60$ @ $0.8\ V_{CES}$	A
<b><math>t_{SC}</math> (SCSOA)</b>	$V_{GE} = 15\text{ V}$ , $V_{CE} = 360\text{ V}$ , $T_J = 125^\circ\text{C}$ $R_G = 33\ \Omega$ , non repetitive	10	$\mu\text{s}$
$P_C$	$T_C = 25^\circ\text{C}$	200	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXSH)



TO-204 AE (IXSM)



G = Gate,  
E = Emitter,

C = Collector,  
TAB = Collector

### Features

- International standard packages
- Guaranteed Short Circuit SOA capability
- Low  $V_{CE(sat)}$ 
  - for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
  - drive simplicity
- Fast Fall Time for switching speeds up to 20 kHz

### Applications

- AC motor speed control
- Uninterruptible power supplies (UPS)
- Welding

### Advantages

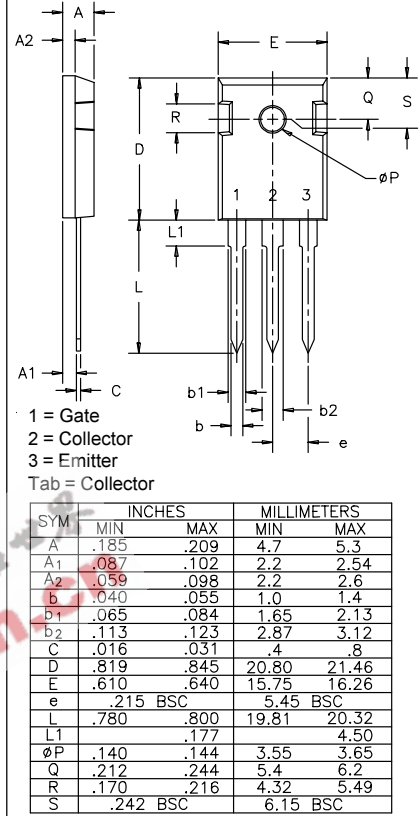
- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 250\ \mu\text{A}$ , $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 2.5\text{ mA}$ , $V_{CE} = V_{GE}$	5		8 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ , $V_{GE} = 0\text{ V}$			$T_J = 25^\circ\text{C}$ : 100 $\mu\text{A}$ $T_J = 125^\circ\text{C}$ : 1 mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$			30N60: 2.5 V 30N60A: 3.0 V

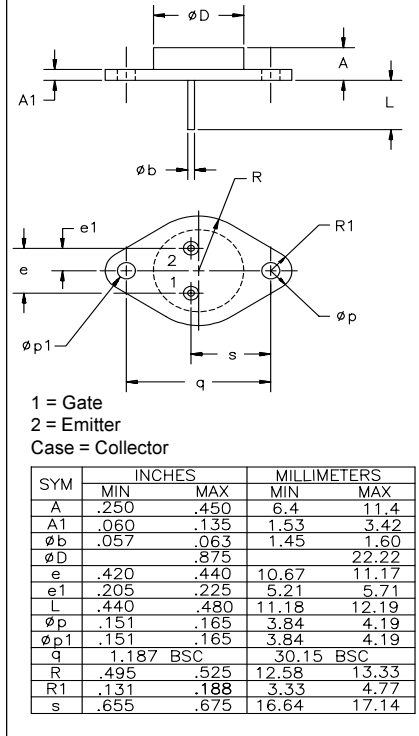
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	7	13	S	
$I_{C(on)}$	$V_{GE} = 15\text{ V}$ , $V_{CE} = 10\text{ V}$		100	A	
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		2760	pF	
$C_{oes}$			240	pF	
$C_{res}$			51	pF	
$Q_g$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		110	nC	
$Q_{ge}$			34	nC	
$Q_{gc}$			47	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ $V_{CE} = 0.8 V_{CES}$ , $R_G = 4.7\ \Omega$ Remarks: Switching times may increase for higher $T_J$ or increased $R_G$		60	ns	
$t_{ri}$			130	ns	
$t_{d(off)}$			400	ns	
$t_{fi}$		30N60	400	ns	
		30N60A	200	ns	
$E_{off}$	$V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$	30N60	5.0	mJ	
		30N60A	2.5	mJ	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ $V_{CE} = 0.8 V_{CES}$ , $R_G = 4.7\ \Omega$ Remarks: Switching times may increase for higher $T_J$ or increased $R_G$		60	ns	
$t_{ri}$			130	ns	
$E_{on}$			1.0	mJ	
$t_{d(off)}$		30N60	540	1000	ns
		30N60A	340	525	ns
$t_{fi}$	30N60	600	1500	ns	
	30N60A	340	700	ns	
$E_{off}$	$V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$	30N60	12	mJ	
		30N60A	6	mJ	
$R_{thJC}$				0.63	KW
$R_{thCK}$			0.25		KW

IXSH 30N60 and IXSH 30N60A characteristic curves are located on the IXSH 30N60U1 and IXSH 30N60AU1 data sheets.

**TO-247 AD Outline**



**TO-204AE Outline**



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025